

Schedule-at-a-Glance – a.m.

Sunday, September 30, 2018

Monday, October 1, 2018

Tuesday, October 2, 2018

Wednesday, October 3, 2018

Thursday, October 4, 2018

Friday, October 5, 2018

7:00-9:30 Breakfast: Vistas Dining Room

7:30-10:30 Registration
(Max Bell Central Foyer)

7:30-8:30 Registration
(Max Bell Central Foyer)

8:45-10:00 Session:
Nanowires
(Max Bell Auditorium)

8:30-9:15 Invited Presentation:
MBE Innovator Award winner
Pallab Bhattacharya
(Max Bell Auditorium)

9:15-10:00 Session:
Novel III-N Growth and
Applications
(Max Bell Auditorium)

8:30-9:00 Invited Presentation:
MBE Young Investigator Award
winner
Paul Simmonds
(Max Bell Auditorium)

9:00-10:00 Session:
Bismuth Alloys
(Max Bell Auditorium)

8:30-10:00 Session:
II-VI Materials and
Heterovalent Growth
(Max Bell Auditorium)

8:45-10:30 Workshop
Welcome and
Workshop Session:
2D Materials
(Max Bell 252)

9:00-10:30
Workshop Session:
Crosscutting
(Max Bell 252)

10:00-10:30 Coffee Break
(Max Bell Foyer)

10:00-10:30 Coffee Break and
Exhibits
(Max Bell Foyer, exhibit rooms)

10:00-10:30 Coffee Break and
Exhibits
(Max Bell Foyer, exhibit rooms)

10:00-10:30 Coffee Break and
Exhibits
(Max Bell Foyer, exhibit rooms)

10:30-10:45 Coffee
Break
(Max Bell Foyer)

10:30-10:45 Coffee
Break
(Max Bell Foyer)

10:30-12:00 Session:
Novel III-V Compounds and
Growth Techniques
(Max Bell Auditorium)

10:30-12:00 Session:
III-Nitrides for Electronics
(Max Bell Auditorium)

10:30-12:00 Session:
Antimonides
(Max Bell Auditorium)

10:30-12:00 Session:
Topological Insulators and
Quantum Computing
(Max Bell Auditorium)

10:45-12:15
Workshop Session:
Layered
Heteroepitaxy
(Max Bell 252)

10:45-12:15
Workshop Session:
Metamorphic
Antimonides
(Max Bell 252)

10:30-12:30
Exhibit Move-Out

12:00-1:30 Lunch: Vistas Dining Room

NAMBE Advisory Board
Lunch Meeting 12:30-1:30

Schedule-at-a-Glance – p.m.

Saturday, September 29, 2018	Sunday, September 30, 2018	Monday, October 1, 2018	Tuesday, October 2, 2018	Wednesday, October 3, 2018	Thursday, October 4, 2018
	1:30 onwards Free afternoon and evening to explore Banff	1:30-3:00 Session: Novel Materials and Oxides (Max Bell Auditorium)	1:30-2:30 Session: Solar Cells 2:30-3:00 Plenary Presentation – Charles Tu (Max Bell Auditorium)	1:30-3:00 Session: Quantum Dots (Max Bell Auditorium)	1:30-3:00 Workshop Session: Topological Insulators (Max Bell 252)
		3:00-3:30 Coffee Break and Exhibits (Max Bell Foyer, exhibit rooms)	3:00-3:30 Coffee Break and Exhibits (Max Bell Foyer, exhibit rooms)	3:00-3:30 Coffee Break (Max Bell Foyer)	3:00-3:15 Coffee Break (Max Bell Foyer)
4:00-8:00 Registration (Max Bell Central Foyer)	3:00-7:00 Exhibit Move-In (Max Bell Centre Rooms 251, 252, 253)	3:30-4:45 Session: 2D Materials and Characterization (Max Bell Auditorium)	3:30-4:00 Exhibits and Networking (Max Bell Foyer, exhibit rooms)	3:30-4:45 Session: Growth and Heterogeneous Integration on Si, Ge (Max Bell Auditorium)	3:15-4:45 Workshop Session: Low Bandgap Antimonides (Max Bell 252)
5:00-8:00 Welcome Reception (Max Bell Foyer)		5:00-6:30 Poster, Exhibits and Networking (Max Bell Lounge, exhibit rooms)	5:30 and 6:00 Buses Depart to Banquet facility (Mountview BBQ)	4:45 Closing of Main Conference and Announcement of Student Awards	
	Riber Users' Meeting	Veeco Users' Meeting			

Sunday Morning, September 30, 2018

MBE - Room Max Bell Auditorium - Session MBE-SuM Nanowires Moderator: Richard Ares, Université de Sherbrooke	
8:45am	MBE-SuM1 Optically Active Dilute-Antimonide Ga(In,Sb)N Nanostructures for Deep-visible Optoelectronics and Solar Fuel Applications, Faqrul A. Chowdhury , Q. Shi, H. Guo, McGill University, Canada; Z. Mi, University of Michigan
9:00am	MBE-SuM2 The Effects of N Incorporation in GaAsSb based Core-shell Nanowires, Prithviraj Deshmukh , M. Sharma, S. Nalamati, North Carolina A&T State University; C.L. Reynolds, Y. Liu, North Carolina State University; S. Iyer, North Carolina A&T State University
9:15am	MBE-SuM3 Growth of GaAsSb Axial Nanowires on Graphene by Molecular Beam Epitaxy, S. Nalamati, M. Sharma, Prithviraj Deshmukh , North Carolina A&T State University; D. Snyder, J. Kronz, Pennsylvania State University; M. Zugger, L. Reynolds, Y. Liu, North Carolina State University; S. Iyer, North Carolina A&T State University
9:30am	MBE-SuM4 Cylindrically Confined Superparamagnetic MnAs Nanocrystals Embedded in Wurtzite (In,Ga)As-(Al,Ga)As Core-shell Nanowires, Janusz Sadowski , Linnaeus University, Sweden; S. Kret, A. Kaleta, B. Kurowska, M. Sawicki, Institute of Physics, Polish Academy of Sciences, Poland
9:45am	MBE-SuM5 Bright Single InAsP Quantum Dots at Telecom Wavelengths in Position-Controlled InP Nanowires, Philip Poole , S. Haffouz, NRC, Canada; K. Zeuner, KTH Royal Institute of Technology, Sweden; D. Dalacu, J. Lapointe, D. Poitras, K. Mnaymneh, X. Wu, M. Couillard, M. Korkusinski, NRC, Canada; E. Scholl, K. Jons, V. Zwiller, KTH Royal Institute of Technology, Sweden; R. Williams, NRC, Canada
10:00am	Break
10:15am	Break
MBE - Room Max Bell Auditorium - Session MBE-SuM Novel III-V Compounds and Growth Techniques Moderator: Amy Liu, IQE Inc.	
10:30am	MBE-SuM9 Continuously-Graded Parabolic Quantum Wells in AlGaAs, Chris Deimert , Z.R. Wasilewski, University of Waterloo, Canada
10:45am	MBE-SuM10 Growth and Characterization of Al _{0.48} In _{0.52} As on InP (100) by Hybrid MBE-CBE for Optoelectronics Applications, Thierno Mamoudou Diallo , A.B. Pougoue Mbeunmi, M. El-Ghouchi, M. Jellite, S. Fafard, R. Arès, A. Boucherif, Université de Sherbrooke, Canada
11:00am	MBE-SuM11 InAlAs/InGaAs Growth on InP(111)A and InP(111)B Substrates with Varying Substrate Offcut Angle, Ida Sadeghi , M.C. Tam, Z.R. Wasilewski, University of Waterloo, Canada
11:15am	MBE-SuM12 Growth and Characterization of Undoped InGaAs by Hybrid MBE-CBE for Optoelectronic Applications, Alex Brice Pougoue Mbeunmi , T.M. Diallo, M. El-Ghouchi, M. Jellite, G. Gomme, A. Boucherif, S. Fafard, R. Ares, Université de Sherbrooke, Canada
11:30am	MBE-SuM13 Epitaxial Growth and Properties of II ₃ V ₂ Semiconductors: Mg ₃ N ₂ and Zn ₃ N ₂ , Peng Wu , T. Tiedje, University of Victoria, Canada
11:45am	MBE-SuM14 Examining the Effects of Strain and TI Content on the Properties and Structure of TlGaAs Films, Kevin Grossklau , J. Ganguly, M. Stevens, J. McElearney, T. Vanderveelde, Tufts University

Monday Morning, October 1, 2018

<p>MBE - Room Max Bell Auditorium - Session MBE-MoM Novel III-N Growth and Applications/III-Nitrides for Electronics Moderator: Thomas Tiedje, University of Victoria, Isaac Hernandez-Calderon, CINVESTAV</p>	
8:30am	INVITED: MBE-MoM1 MBE Innovator Award Talk: Evolution, Development and Commercialization of the Quantum Dot Laser: Brief History and Recent Progress, <i>Pallab Bhattacharya</i> , University of Michigan
8:45am	Invited talk continues.
9:00am	Invited talk continues.
9:15am	MBE-MoM4 High Growth Rate Plasma Considerations for Indium-rich III-nitrides, <i>Evan Clinton, E. Vadiie, W.A. Doolittle</i> , Georgia Institute of Technology
9:30am	MBE-MoM5 Molecular Beam Epitaxy of III-Nitride Nanowires on Amorphous and Nanocrystalline Metals, <i>Brelon May, E. Hettiaratchy, R. Myers</i> , The Ohio State University
9:45am	MBE-MoM6 RF-Plasma MBE Growth of Epitaxial Metallic TaN _x Transition Metal Nitride Films on SiC, <i>D. Scott Katzer, N. Nepal, M. Hardy, B. Downey, D. Storm, D. Meyer</i> , U.S. Naval Research Laboratory
10:00am	Break & Exhibits
10:15am	Break & Exhibits
<p>MBE - Room Max Bell Auditorium - Session MBE-MoM III-Nitrides for Electronics Moderator: Maria Tamargo, City College of New York, City University of New York</p>	
10:30am	MBE-MoM9 Magneto-Photoluminescence Properties of an AlGa _N /Ga _N 2DEG Grown on Bulk Ga _N , <i>Stefan Schmult</i> , TU Dresden, Germany; <i>V.V. Solovyev</i> , Institute of Solid State Physics RAS, Russia; <i>S. Wirth</i> , Max-Planck-Institute for Chemical Physics of Solids, Germany; <i>A. Grosser</i> , NaMLab gGmbH, Germany; <i>T. Mikolajick</i> , TU Dresden & NaMLab gGmbH, Germany; <i>I.V. Kukushkin</i> , Institute of Solid State Physics RAS, Russia
10:45am	MBE-MoM10 Kinetically Limited Growth of High Scandium Fraction Scandium Aluminum Nitride, <i>Matthew Hardy, B. Downey, N. Nepal, D. Storm, D.S. Katzer, D. Meyer</i> , U.S. Naval Research Laboratory
11:00am	MBE-MoM11 Low Resistivity Al-rich AlGa _N Grown by Plasma-assisted Molecular Beam Epitaxy, <i>Ayush Pandey</i> , University of Michigan; <i>X. Liu</i> , McGill University, Canada; <i>D. Laleyan, K. Mashooq, E. Reid, W. Shin, P. Bhattacharya, Z. Mi</i> , University of Michigan
11:15am	MBE-MoM12 RF-MBE Growth of AlN/GaN/AlN Resonant Tunneling Diodes on Freestanding GaN and GaN Templates, <i>David Storm</i> , U.S. Naval Research Laboratory; <i>T. Growden</i> , The Ohio State University; <i>W. Zhang</i> , Wright State University; <i>D.S. Katzer, M. Hardy, D. Meyer</i> , U.S. Naval Research Laboratory; <i>E. Brown</i> , Wright State University; <i>P. Berger</i> , The Ohio State University
11:30am	MBE-MoM13 Low-resistance GaN Homojunction Tunnel Diodes and Low Voltage Drop Tunnel Contacts, <i>E. Vadiie, Evan Clinton, W.A. Doolittle</i> , Georgia Institute of Technology
11:45am	MBE-MoM14 On the Efficiency and Long-term Stability of MBE-grown III-Nitride Nanostructures for Unassisted Overall Water Splitting, <i>Faqur A. Chowdhury, H. Tran, H. Guo</i> , McGill University, Canada; <i>Z. Mi</i> , University of Michigan

Monday Afternoon, October 1, 2018

MBE - Room Max Bell Auditorium - Session MBE-MoA Novel Materials and Oxides Moderator: Joshua Zide, University of Delaware	
1:30pm	MBE-MoA1 Epitaxial Stabilization of Monoclinic Fe ₂ O ₃ on β-Ga ₂ O ₃ , <i>John Jamison, B. May, R. Myers</i> , The Ohio State University
1:45pm	MBE-MoA2 Homo- and Hetero-epitaxial Growth of β-Ga ₂ O ₃ Thin Films by Molecular Beam Epitaxy, <i>Neeraj Nepal, D.S. Katzer, B. Downey, V. Wheeler, M. Hardy, D. Storm, D. Meyer</i> , U.S. Naval Research Laboratory
2:00pm	MBE-MoA3 Epitaxial Growth and Electronic Structure of Semiconducting Half-Heusler FeVSb, <i>Estiaque Haidar Shourov, P.J. Strohbeen, D. Du</i> , University of Wisconsin Madison; <i>J. McChesney</i> , Argonne National Laboratory; <i>A. Janotti</i> , University of Delaware; <i>J. Kawasaki</i> , University of Wisconsin Madison
2:15pm	MBE-MoA4 Growth of Candidate Polar Metal Hexagonal Half Heuslers, <i>Dongxue Du, J. Kawasaki</i> , University of Wisconsin Madison
2:30pm	MBE-MoA5 Optimizing Cesium Antimonide Photocathode Performance Using Real-time <i>In-situ</i> Monitoring of Photoemissive Properties, <i>Mark Hoffbauer</i> , Los Alamos National Laboratory; <i>S. Celestin</i> , Northeastern University; <i>V. Pavlenko, F. Liu, N. Moody</i> , Los Alamos National Laboratory
2:45pm	MBE-MoA6 Optically Triggered Semiconductor Hyperbolic Metamaterial for Controlled Single Photon Emission, <i>Kurt Eyink, H. Haugan, V. Pustovit, A. Urbas</i> , Air Force Research Laboratory
3:00pm	Break & Exhibit
3:15pm	Break & Exhibit
MBE - Room Max Bell Auditorium - Session MBE-MoA 2D Materials and Characterization Moderator: Geoffrey Gardner, Microsoft Research	
3:30pm	MBE-MoA9 Epitaxy of <i>M</i> /graphene/Ge (<i>M</i> = Fe, Sb) Heterostructures: Testing the Limits of Remote Heteroepitaxy, <i>Patrick J. Strohbeen, E.H. Shourov, V. Saraswat, D. Du, M.S. Arnold, J. Kawasaki</i> , University of Wisconsin Madison
3:45pm	MBE-MoA10 Molecular Beam Epitaxy of MoSe ₂ Directly on Si, <i>Elline Hettiaratchy, B. May, R. Myers</i> , The Ohio State University
4:00pm	MBE-MoA11 Atomic Scale Characterization Showing Kinetic Compositional Instability and Phase Separation in MBE-grown InGaAs, <i>Michael Yakes, M. Twigg, N. Kotulak, N. Mahadik, S. Tomasulo</i> , U.S. Naval Research Laboratory
4:15pm	MBE-MoA12 Investigation of Gallium-related Defects in III/V Epitaxial Layers, <i>Yossi Cohen, O. Klin, I. Grimberg, N. Yaron, E. Weiss</i> , Semiconductor Devices Company, Israel
4:30pm	MBE-MoA13 Acoustic Nanostructures for Charge Carrier Confinement in GaAs/Al _x Ga _{1-x} As Multiple Quantum Wells, <i>Kevin Vallejo, C. Schuck, T. Garrett</i> , Boise State University; <i>Z. Hua, D.H. Hurley</i> , Idaho National Laboratory; <i>P. Simmonds</i> , Boise State University
4:45pm	Posters, Exhibits, and Networking

MBE

Room Elder Tom Crane Bear - Session MBE-MoP

MBE-Poster Session

4:45pm

MBE-MoP1 Hydrogen Permeation Behavior of BN film, *Motonori Tamura*, The University of Electro-Communications, Japan

MBE-MoP3 Growth of Pure Wurtzite InGaAs Nanowires for Photovoltaic and Energy Harvesting Applications, *Hangkyu Kang, M. Baik*, Yonsei University, Republic of Korea; *B. Yoo*, Hanyang University, Republic of Korea; *J. Song*, Korea Institute of Science and Technology, Republic of Korea; *M.-H. Cho*, Yonsei University, Republic of Korea

MBE-MoP4 Effect of ex-situ Passivation of the GaAsSb Nanowires, *Manish Sharma, J. Li, S. Iyer*, North Carolina A&T State University

MBE-MoP5 Study of As-rich Interfaces with Exponentially Decaying As Content within InAs/AlSb Superlattices, *Yunong Hu, M.C. Tam, Z.R. Wasilewski*, University of Waterloo, Canada

MBE-MoP6 Radio-frequency Modulated Terahertz Radiation Induced by Self-oscillations of the Current in Weakly-coupled GaAs/AlGaAs Superlattices, *Gulya Rasulova*, P.N.Lebedev Physical Institute of RAS, Russian Federation

MBE-MoP7 The Characteristics of Phototransistor based on the Grown MoSe₂ by Molecular Beam Epitaxy, *Yoon-Ho Choi, J.-H. Jeong, G.-H. Kwon, H.-S. Kim*, Yonsei University, Republic of Korea; *H. Kim*, Sungkyunkwan University, Republic of Korea; *M.-H. Cho*, Yonsei University, Republic of Korea

MBE-MoP8 Experimental Determination of Band Overlap in Type II InAs/GaSb Superlattice based on Temperature Dependent Photoluminescence Signal, *J. Huang, Y. Zhang, Y. Cao, K. Liu, W. Huang, S. Luo, H. Ji, T. Yang, Wenquan Ma*, Institute of Semiconductors, Chinese Academy of Sciences, China

MBE-MoP10 Significantly Enhanced Performances of 1.3 μm InAs/GaAs Quantum Dot Lasers by Direct Si-doping, *Z. Lv, Z. Zhang, Tao Yang*, Institute of Semiconductors, Chinese Academy of Sciences, China

MBE-MoP11 Effect of in-situ Annealing on the GaAsSb Nanowire-based Photodetector, *Manish Sharma, E. Ahmad, M. Parakh, R. Pokharel, S. Iyer*, North Carolina A&T State University

MBE-MoP12 Reduced Heating Effects in MBE Grown Nanowire Array LEDs, *S. Yang*, McGill University, Canada; *A. Tian*, St. Maximilian Kolbe CHS, Canada; *Yongyuan Zang*, McGill University, Canada

MBE-MoP13 Effect of Column Diameter and Height on Optical Properties of Regularly Arranged GaN Nanocolumn Grown by rf-MBE, *Hiroto Sekiguchi, Y. Higashi, K. Yamane, H. Okada, A. Wakahara*, Toyohashi University of Technology, Japan; *K. Kishino*, Sophia University, Japan

Tuesday Morning, October 2, 2018

MBE - Room Max Bell Auditorium - Session MBE-TuM Bismuth Alloys Moderator: Richard Mirin, National Institute of Standards and Technology	
8:30am	INVITED: MBE-TuM1 MBE Young Investigator Award Talk: Tensile-strained Self-assembly of Quantum Dots for Entangled Photon Sources and Band Structure Engineering, <i>Paul Simmonds</i> , Boise State University
8:45am	Invited talk continues.
9:00am	MBE-TuM3 Mechanisms of Compositional Inhomogeneities in Bismide Films, <i>C. Tait, B. Carter, V. Caro, Joanna Millunchick</i> , University of Michigan
9:15am	MBE-TuM4 In-situ UV Irradiation on the Uniformity and Optical Properties of GaAsBi Epi-layers Grown by MBE, <i>Daniel Beaton</i> , ScientaOmicron
9:30am	MBE-TuM5 Manipulating Film and Underlayer Strain to Understand Composition Modulation in GaAsBi, <i>Margaret Stevens, K. Grossklous, J. McElearney, T. Vandervelde</i> , Tufts University
9:45am	MBE-TuM6 Long-Wavelength InAs-based Interband Cascade Lasers Grown by MBE, <i>James Gupta, X. Wu, G.C. Aers</i> , National Research Council of Canada; <i>Y. Li, L. Li, W. Huang, R.Q. Yang</i> , University of Oklahoma
10:00am	Break & Exhibits
10:15am	Break & Exhibits
MBE - Room Max Bell Auditorium - Session MBE-TuM Antimonides Moderator: James Gupta, National Research Council of Canada	
10:30am	MBE-TuM9 Atomically Smooth InSb Quantum Wells on GaAs Substrates, <i>Yinqiu Shi, E. Bergeron, F. Sfigakis, J. Baugh, Z.R. Wasilewski</i> , University of Waterloo, Canada
10:45am	MBE-TuM10 Narrow Bandgap InAsSb Detector on Digital Alloy AllnSb Metamorphic Buffer, <i>Vinita Dahiya, A. Kazemi</i> , The Ohio State University; <i>E. Fraser</i> , Intelligent Epitaxy Technology, Inc.; <i>J. Deitz, J. Boyer, S.H. Lee</i> , The Ohio State University; <i>P. Pinsukanjana</i> , Intelligent Epitaxy Technology, Inc.; <i>T. Grassman, S. Krishna</i> , The Ohio State University
11:00am	MBE-TuM11 Molecular Beam Epitaxy of Wide-Bandgap InAlAsSb, <i>Stephanie Tomasulo</i> , U.S. Naval Research Laboratory; <i>M. Gonzalez</i> , Sotera Defense Solutions; <i>M. Lumb</i> , The George Washington University; <i>M. Twigg, I. Vurgaftman, J. Meyer, R. Walters, M. Yakes</i> , U.S. Naval Research Laboratory
11:15am	MBE-TuM12 Minority Carrier Lifetime and Recombination Dynamics in Strain-Balanced GaInAs/InAsSb Superlattices, <i>Preston T. Webster, E.H. Steenbergen, G. Ariyawansa, C.J. Reyner</i> , Air Force Research Laboratory; <i>J.K. Kim</i> , Sandia National Laboratories
11:30am	MBE-TuM13 Inhibited Hot-Carrier Cooling in InAs/AlAs _{1-x} Sb _x Quantum Wells, <i>H. Esmailpour, V. Whiteside</i> , University of Oklahoma; <i>H. Piyathilaka</i> , West Virginia University; <i>S. Vijayaragunathan, B. Wang</i> , University of Oklahoma; <i>E. Adcock-Smith, K. Roberts</i> , University of Tulsa; <i>T. Mishima, Michael Santos</i> , University of Oklahoma; <i>A. Bristow</i> , West Virginia University; <i>I. Sellers</i> , University of Oklahoma
11:45am	MBE-TuM14 Observation of Interface Electronic States from InAs/GaSb Multi Quantum Wells Grown by Molecular Beam Epitaxy, <i>S. Alyamani, Jong Su Kim, J.C. Shin</i> , Yeungnam University, Korea; <i>S.J. Lee, J.O. Kim</i> , Korea Research Institute of Standards and Science, Korea; <i>S.H. Lee, V. Dahiya, S. Krishna</i> , The Ohio State University

Tuesday Afternoon, October 2, 2018

MBE - Room Max Bell Auditorium - Session MBE-TuA Solar Cells Moderator: Paul Simmonds, Boise State University	
1:30pm	MBE-TuA1 Smart Stacked InGaP/GaAs/GaAs//Si Quadruple-Junction Solar Cells Grown using Molecular Beam Epitaxy, <i>Takeyoshi Sugaya</i> , National Institute of Advanced Industrial Science and Technology (AIST), Japan
1:45pm	MBE-TuA2 2.0 – 2.2 eV AlGaInP Solar Cells Grown by MBE, <i>Yukun Sun</i> , Yale University; <i>S. Fan</i> , University of Illinois Urbana-Champaign; <i>J. Faucher</i> , Yale University; <i>B. Li, M.L. Lee</i> , University of Illinois Urbana-Champaign
2:00pm	MBE-TuA3 Optoelectronic Analysis of MBE Grown Symmetric and Asymmetric 1 eV Dilute Nitride Quantum Well Solar Cells, <i>Khim Kharel</i> , <i>M. Fitchette</i> , University of Houston; <i>K. Shervin</i> , Alta Device; <i>W. Wang</i> , First Solar Cell; <i>A. Freundlich</i> , University of Houston
2:15pm	MBE-TuA4 Development of Hybrid Gas-source MBE to make Thin Films of Sulfide Perovskites and Related Complex Chalcogenides, <i>S. Filippone, Y. Li, Rafael Jaramillo</i> , Massachusetts Institute of Technology
2:30pm	INVITED: MBE-TuA5 Reflections on NAMBE and MBE, <i>Charles Tu</i> , University of California - San Diego
2:45pm	Invited talk continues.
3:00 pm	Break, Exhibits, and Networking

Wednesday Morning, October 3, 2018

MBE - Room Max Bell Auditorium - Session MBE-WeM II-VI Materials and Heterovalent Growth Moderator: Philip Poole, NRC	
8:30am	MBE-WeM1 High-Reflectivity Heterovalent Distributed Bragg Reflectors for Infrared Resonant Cavity Applications, <i>Maxwell Lassise, B. Tracy, D. Smith, Y.-H. Zhang</i> , Arizona State University
8:45am	MBE-WeM2 Photoluminescence Characterization of a 1 ML CdSe Fully-Strained Ultra-Thin Quantum Well with very Thin ZnSe Barriers, <i>A.D. Alfaro-Martínez, DNYN, CINVESTAV, Mexico; F. Sutara, Isaac Hernández-Calderón</i> , CINVESTAV, Mexico
9:00am	MBE-WeM3 Hybrid II-VI/III-V Infrared Photodetectors, <i>Marcel Claro</i> , City College of New York, City University of New York; <i>Y. Kaya</i> , Princeton University; <i>T. Garcia, C. Forrester, V. Deligiannakis</i> , City College of New York, City University of New York; <i>C. Gmachl</i> , Princeton University; <i>M. Tamargo</i> , City College of New York, City University of New York
9:15am	MBE-WeM4 Cd ₃ As ₂ /II-VI Heterostructures on (111) GaAs, <i>Anthony Rice, K. Park, K. Alberi</i> , National Renewable Energy Laboratory
9:30am	MBE-WeM5 Demonstration of the Growth of ZnCdTe/ZnTe Quantum Wells with Variable Composition by Submonolayer Pulsed Beam Epitaxy (SPBE), <i>F. Sutara, Isaac Hernández-Calderón</i> , CINVESTAV, Mexico
9:45am	MBE-WeM6 Interface Modification in Type-II ZnCdSe/Zn(Cd)Te QDs, <i>Vasilios Deligiannakis, S. Dhomkar, M. Claro</i> , City College of New York, City University of New York; <i>I. Kuskovsky</i> , Queens College; <i>M. Tamargo</i> , City College of New York, City University of New York
10:00am	Break & Exhibits
10:15am	Break & Exhibits
MBE - Room Max Bell Auditorium - Session MBE-WeM Topological Insulators and Quantum Computing Moderator: Michael Santos, University of Oklahoma	
10:30am	MBE-WeM9 Molecular Beam Epitaxy Growth of Near Surface InAs Two-dimensional Electron Gas for Topological Quantum Computation, <i>Candice Thomas, A. Hatke, M. Capano, T. Wang, R. Diaz, S. Gronin, G. Gardner, M. MANFRA</i> , Purdue University
10:45am	MBE-WeM10 InAs Surface 2DEG and Interface Characterization of InAs/Al Structures Using Josephson Junctions, <i>Kaushini Wickramasinghe, W. Mayer, J. Yuan, K. Sardashti, J. Shabani</i> , New York University
11:00am	MBE-WeM11 Epitaxial Growth of Superconducting Thin Aluminum Films on InAs for Topological Quantum Computing, <i>Geoffrey Gardner</i> , Microsoft Research; <i>C. Thomas, T. Wang</i> , Purdue University; <i>S. Gronin</i> , Microsoft Research; <i>M. Capano, M. MANFRA</i> , Purdue University
11:15am	MBE-WeM12 Morphological Control Over (Bi _x In _{1-x}) ₂ Se ₃ Grown on GaAs, <i>Theresa Ginley, S. Law</i> , University of Delaware
11:30am	MBE-WeM13 Dielectric Functions of MBE-grown Bi ₂ (Te _{1-x} Se _x) ₃ Thin Films, <i>E. Holmgren, J. Lyons, Frank Peiris</i> , Kenyon College; <i>X. Li, X. Liu, M. Dobrowolska, J. Furdyna</i> , University of Notre Dame
11:45am	MBE-WeM14 MBE Growth and Properties of Bi ₂ Se ₃ /Sb ₂ Te ₃ p-n-p-n Short-period Superlattices, <i>Ido Levy, T. Garcia, H. Deng, S. Alsheimer, L. Krusin-Elbaum, M. Tamargo</i> , City College of New York, City University of New York

Wednesday Afternoon, October 3, 2018

MBE Room Max Bell Auditorium - Session MBE-WeA Quantum Dots Moderator: Shanthi Iyer, North Carolina A&T State University	
1:30pm	MBE-WeA1 96 GHz Colliding Pulse Mode-locked Quantum Dot Lasers Grown on Silicon, <i>Justin Norman, S. Liu, D. Jung, M. Kennedy, A. Gossard, J. Bowers</i> , University of California, Santa Barbara
1:45pm	MBE-WeA2 InAs/GaAs Submonolayer (SML) Quantum Dot-based Semiconductor Saturable Absorber Mirrors (SESAMs), <i>Sadhvikas Addamane</i> , University of New Mexico; <i>A. Laurain, J. Moloney</i> , University of Arizona; <i>G. Balakrishnan</i> , University of New Mexico
2:00pm	MBE-WeA3 Strain-Compensated Quantum Dot Cascade Lasers, <i>Feng-Qi Liu</i> , Institute of Semiconductors, Chinese Academy of Sciences, China
2:15pm	MBE-WeA4 (111)-oriented Stranski-Krastanov Quantum Dots Optimized for Entangled Photon Emission, <i>Christopher Schuck, K. Vallejo, S. Roy, T. Garrett, K. Sautter</i> , Boise State University; <i>B.L. Liang, D. Huffaker</i> , University of California, Los Angeles; <i>C. Palmstøm</i> , University of California, Santa Barbara; <i>P. Simmonds</i> , Boise State University
2:30pm	MBE-WeA5 Optimization of InAs Quantum Dots for Scintillation Applications, <i>Michael Yakimov, V. Tokranov, K. Dropiewski, A. Minns</i> , SUNY Polytechnic Institute; <i>P. Murat</i> , Fermi National Accelerator Laboratory; <i>S. Oktyabrsky</i> , SUNY Polytechnic Institute
2:45pm	MBE-WeA6 Tensile-Strained Ge Quantum Dots on (111)A Surfaces, <i>Kathryn Sautter, C. Schuck, T. Garrett, A. Weltner, K. Vallejo, P. Simmonds</i> , Boise State University
3:00pm	Break
3:15pm	Break
MBE Room Max Bell Auditorium - Session MBE-WeA Growth and Heterogeneous Integration on Si, Ge Moderator: Preston T. Webster, Air Force Research Laboratory	
3:30pm	MBE-WeA9 Relaxed GaP on Si with Low Threading Dislocation Density, <i>Ryan Hool, Y. Chai, P. Dhingra, B. Eng</i> , University of Illinois Urbana-Champaign; <i>Y. Sun</i> , Yale University; <i>S. Fan</i> , University of Illinois Urbana-Champaign; <i>K.N. Yaung</i> , Yale University; <i>M.L. Lee</i> , University of Illinois Urbana-Champaign
3:45pm	MBE-WeA10 Defect Creation in Low Deteriorated Polar/polar (GaAsSb-GaAs) and Polar/non-polar (GaP-Si) Epitaxial Structures, <i>Abhinandan Gangopadhyay, A. Maros, C. Zhang, A. Boley, N. Faleev, D. Smith, C. Honsberg</i> , Arizona State University
4:00pm	MBE-WeA11 Epitaxial III-V Growths on 0.1-mm Grain-size Polycrystalline Germanium Thin-films, <i>Abhinav Chikhalkar, C. Zhang, N. Faleev</i> , Arizona State University; <i>E. McClure, S. Hubbard</i> , Rochester Institute of Technology; <i>C. Honsberg, R. King</i> , Arizona State University
4:15pm	MBE-WeA12 Grating Coupled Quantum Well Infrared Photodetector on a Si Substrate, <i>HoSung Kim</i> , University of Waterloo, Canada; <i>G.H. Ryu, S.Y. Ahn</i> , Korea Institute of Science and Technology, Korea; <i>Z.R. Wasilewski</i> , University of Waterloo, Canada; <i>W.J. Choi</i> , Korea Institute of Science and Technology, Korea
4:30pm	MBE-WeA13 Direct MBE Growth of Metamorphic nBn Infrared Photodetectors on 150 mm Ge-Si Substrates for Heterogeneous Integration, <i>Joel Fastenau, D. Lubyshev, S. Nelson</i> , IQE Inc.; <i>A. Morgan, S. Edwards</i> , IQE Silicon, UK; <i>M. Fethers, H. Krysiak, J. Zeng, M. Kattner, P. Frey, A. Liu</i> , IQE Inc.
4:45pm	Closing Remarks and Annoucement of Student Awards
5:00pm	

Bold page numbers indicate presenter

— A —

Adcock-Smith, E.: MBE-TuM13, 21
 Addamane, S.: MBE-WeA2, **24**
 Aers, G.C.: MBE-TuM6, 21
Ahmad, E.: MBE-MoP11, 20
 Ahn, S.Y.: MBE-WeA12, 24
 Alberi, K.: MBE-WeM4, 23
 Alfaro-Martínez, A.D.: MBE-WeM2, 23
 Alsheimer, S.: MBE-WeM14, 23
 Alyamani, S.: MBE-TuM14, 21
 Ares, R.: MBE-SuM12, 17
 Arès, R.: MBE-SuM10, 17
 Ariyawansa, G.: MBE-TuM12, 21
 Arnold, M.S.: MBE-MoA9, 19

— B —

Baik, M.: MBE-MoP3, 20
 Balakrishnan, G.: MBE-WeA2, 24
 Baugh, J.: MBE-TuM9, 21
 Beaton, D.: MBE-TuM4, **21**
 Berger, P.: MBE-MoM12, 18
 Bergeron, E.: MBE-TuM9, 21
 Bhattacharya, P.: MBE-MoM1, **18**; MBE-MoM11, 18
 Boley, A.: MBE-WeA10, 24
 Boucherif, A.: MBE-SuM10, 17; MBE-SuM12, 17
 Bowers, J.: MBE-WeA1, 24
 Boyer, J.: MBE-TuM10, 21
 Bristow, A.: MBE-TuM13, 21
 Brown, E.: MBE-MoM12, 18

— C —

Cao, Y.: MBE-MoP8, 20
 Capano, M.: MBE-WeM11, 23; MBE-WeM9, 23
 Caro, V.: MBE-TuM3, 21
 Carter, B.: MBE-TuM3, 21
 Celestin, S.: MBE-MoA5, 19
 Chai, Y.: MBE-WeA9, 24
 Chikhalkar, A.: MBE-WeA11, **24**
 Cho, M.-H.: MBE-MoP3, 20; MBE-MoP7, 20
 Choi, W.J.: MBE-WeA12, 24
 Choi, Y.-H.: MBE-MoP7, **20**
 Chowdhury, F.A.: MBE-MoM14, **18**; MBE-SuM1, 17
 Claro, M.: MBE-WeM3, **23**; MBE-WeM6, 23
 Clinton, E.: MBE-MoM13, **18**; MBE-MoM4, **18**
 Cohen, Y.: MBE-MoA12, **19**
 Couillard, M.: MBE-SuM5, 17

— D —

Dahiya, V.: MBE-TuM10, **21**; MBE-TuM14, 21
 Dalacu, D.: MBE-SuM5, 17
 Deimert, C.: MBE-SuM9, **17**
 Deitz, J.: MBE-TuM10, 21
 Deligiannakis, V.: MBE-WeM3, 23; MBE-WeM6, **23**
 Deng, H.: MBE-WeM14, 23
 Deshmukh, P.: MBE-SuM2, **17**; MBE-SuM3, **17**
 Dhingra, P.: MBE-WeA9, 24
 Dhomkar, S.: MBE-WeM6, 23
 Diallo, T.M.: MBE-SuM10, **17**; MBE-SuM12, 17
 Diaz, R.: MBE-WeM9, 23
 Dobrowolska, M.: MBE-WeM13, 23
 Doolittle, W.A.: MBE-MoM13, 18; MBE-MoM4, 18
 Downey, B.: MBE-MoA2, 19; MBE-MoM10, 18; MBE-MoM6, 18
 Dropiewski, K.: MBE-WeA5, 24
 Du, D.: MBE-MoA3, 19; MBE-MoA4, **19**; MBE-MoA9, 19

— E —

Edwards, S.: MBE-WeA13, 24

El-Gahouchi, M.: MBE-SuM10, 17; MBE-SuM12, 17
 Eng, B.: MBE-WeA9, 24
 Esmailpour, H.: MBE-TuM13, 21
 Eyink, K.: MBE-MoA6, **19**

— F —

Fafard, S.: MBE-SuM10, 17; MBE-SuM12, 17
 Faleev, N.: MBE-WeA10, 24; MBE-WeA11, 24
 Fan, S.: MBE-TuA2, 22; MBE-WeA9, 24
 Fastenau, J.: MBE-WeA13, **24**
 Faucher, J.: MBE-TuA2, 22
 Fethers, M.: MBE-WeA13, 24
 Filippone, S.: MBE-TuA4, 22
 Fitchette, M.: MBE-TuA3, 22
 Forrester, C.: MBE-WeM3, 23
 Fraser, E.: MBE-TuM10, 21
 Freundlich, A.: MBE-TuA3, 22
 Frey, P.: MBE-WeA13, 24
 Furdyna, J.: MBE-WeM13, 23

— G —

Gangopadhyay, A.: MBE-WeA10, **24**
 Ganguly, J.: MBE-SuM14, 17
 Garcia, T.: MBE-WeM14, 23; MBE-WeM3, 23
 Gardner, G.: MBE-WeM11, **23**; MBE-WeM9, 23
 Garrett, T.: MBE-WeA4, 24
 Ginley, T.: MBE-WeM12, **23**
 Gmachl, C.: MBE-WeM3, 23
 Gomme, G.: MBE-SuM12, 17
 Gonzalez, M.: MBE-TuM11, 21
 Gossard, A.: MBE-WeA1, 24
 Grassman, T.: MBE-TuM10, 21
 Grimberg, I.: MBE-MoA12, 19
 Gronin, S.: MBE-WeM11, 23; MBE-WeM9, 23
 Grosser, A.: MBE-MoM9, 18
 Grossklaus, K.: MBE-SuM14, **17**; MBE-TuM5, 21
 Growden, T.: MBE-MoM12, 18
 Guo, H.: MBE-MoM14, 18; MBE-SuM1, 17
 Gupta, J.: MBE-TuM6, **21**

— H —

Haffouz, S.: MBE-SuM5, 17
 Hardy, M.: MBE-MoA2, 19; MBE-MoM10, **18**; MBE-MoM12, 18; MBE-MoM6, 18
 Hatke, A.: MBE-WeM9, 23
 Haugan, H.: MBE-MoA6, 19
 Hernández-Calderón, I.: MBE-WeM2, **23**; MBE-WeM5, **23**
 Hettiaratchy, E.: MBE-MoA10, **19**; MBE-MoM5, 18
 Higashi, Y.: MBE-MoP13, 20
 Hoffbauer, A.: MBE-MoA5, **19**
 Holmgren, E.: MBE-WeM13, 23
 Honsberg, C.: MBE-WeA10, 24; MBE-WeA11, 24
 Hool, R.: MBE-WeA9, **24**
 Hu, Y.: MBE-MoP5, **20**
 Huang, J.: MBE-MoP8, 20
 Huang, W.: MBE-MoP8, 20; MBE-TuM6, 21
 Hubbard, S.: MBE-WeA11, 24
 Huffaker, D.: MBE-WeA4, 24

— I —

Iyer, S.: **MBE-MoP11, 20**; **MBE-MoP4, 20**; MBE-SuM2, 17; MBE-SuM3, 17

— J —

Jamison, J.: MBE-MoA1, **19**
 Janotti, A.: MBE-MoA3, 19
 Jaramillo, R.: MBE-TuA4, **22**
 Jellite, M.: MBE-SuM10, 17; MBE-SuM12, 17
 Jeong, J.-H.: MBE-MoP7, 20
 Ji, H.: MBE-MoP8, 20
 Jons, K.: MBE-SuM5, 17
 Jung, D.: MBE-WeA1, 24

— K —

Kaleta, A.: MBE-SuM4, 17
 Kang, H.: MBE-MoP3, **20**
 Kattner, M.: MBE-WeA13, 24
 Katzer, D.S.: MBE-MoA2, 19; MBE-MoM10, 18; MBE-MoM12, 18; MBE-MoM6, **18**
 Kawasaki, J.: MBE-MoA3, 19; MBE-MoA4, 19; MBE-MoA9, 19
 Kaya, Y.: MBE-WeM3, 23
 Kazemi, A.: MBE-TuM10, 21
 Kennedy, M.: MBE-WeA1, 24
 Kharel, K.: MBE-TuA3, **22**
 Kim, H.: MBE-MoP7, 20
 Kim, H.S.: MBE-WeA12, **24**
 Kim, H.-S.: MBE-MoP7, 20
 Kim, J.K.: MBE-TuM12, 21
 Kim, J.O.: MBE-TuM14, 21
 Kim, J.S.: MBE-TuM14, **21**
 King, R.: MBE-WeA11, 24
 Kishino, K.: MBE-MoP13, 20
 Klin, O.: MBE-MoA12, 19
 Korkusinski, M.: MBE-SuM5, 17
 Kotulak, N.: MBE-MoA11, 19
 Kret, S.: MBE-SuM4, 17
 Krishna, S.: MBE-TuM10, 21; MBE-TuM14, 21
 Kronz, J.: MBE-SuM3, 17
 Krusin-Elbaum, L.: MBE-WeM14, 23
 Krysiak, H.: MBE-WeA13, 24
 Kukushkin, I.V.: MBE-MoM9, 18
 Kurowska, B.: MBE-SuM4, 17
 Kuskovsky, I.: MBE-WeM6, 23
 Kwon, G.-H.: MBE-MoP7, 20

— L —

Laleyan, D.: MBE-MoM11, 18
 Lapointe, J.: MBE-SuM5, 17
 Lassise, M.: MBE-WeM1, **23**
 Laurain, A.: MBE-WeA2, 24
 Law, S.: MBE-WeM12, 23
 Lee, M.L.: MBE-TuA2, 22; MBE-WeA9, 24
 Lee, S.H.: MBE-TuM10, 21; MBE-TuM14, 21
 Lee, S.J.: MBE-TuM14, 21
 Levy, I.: MBE-WeM14, **23**
 Li, B.: MBE-TuA2, 22
Li, J.: MBE-MoP4, 20
 Li, L.: MBE-TuM6, 21
 Li, X.: MBE-WeM13, 23
 Li, Y.: MBE-TuA4, 22; MBE-TuM6, 21
 Liang, B.L.: MBE-WeA4, 24
 Liu, A.: MBE-WeA13, 24
 Liu, F.: MBE-MoA5, 19
 Liu, F.-Q.: MBE-WeA3, **24**
 Liu, K.: MBE-MoP8, 20
 Liu, S.: MBE-WeA1, 24
 Liu, X.: MBE-MoM11, 18; MBE-WeM13, 23
 Liu, Y.: MBE-SuM2, 17; MBE-SuM3, 17
 Lubyshev, D.: MBE-WeA13, 24
 Lumb, M.: MBE-TuM11, 21
 Luo, S.: MBE-MoP8, 20
 Lv, Z.: MBE-MoP10, 20
 Lyons, J.: MBE-WeM13, 23

— M —

Ma, W.: MBE-MoP8, **20**
 Mahadik, N.: MBE-MoA11, 19
 MANFRA, M.: MBE-WeM11, 23; MBE-WeM9, 23
 Maros, A.: MBE-WeA10, 24
 Mashooq, K.: MBE-MoM11, 18
 May, B.: MBE-MoA1, 19; MBE-MoA10, 19; MBE-MoM5, **18**
 Mayer, W.: MBE-WeM10, 23
 McChesney, J.: MBE-MoA3, 19
 McClure, E.: MBE-WeA11, 24

Author Index

- McElearney, J.: MBE-SuM14, 17; MBE-TuM5, 21
Meyer, D.: MBE-MoA2, 19; MBE-MoM10, 18; MBE-MoM12, 18; MBE-MoM6, 18
Meyer, J.: MBE-TuM11, 21
Mi, Z.: MBE-MoM11, 18; MBE-MoM14, 18; MBE-SuM1, 17
Mikolajick, T.: MBE-MoM9, 18
Millunchick, J.: MBE-TuM3, **21**
Minns, A.: MBE-WeA5, 24
Mishima, T.: MBE-TuM13, 21
Mnaymneh, K.: MBE-SuM5, 17
Moloney, J.: MBE-WeA2, 24
Moody, N.: MBE-MoA5, 19
Morgan, A.: MBE-WeA13, 24
Murat, P.: MBE-WeA5, 24
Myers, R.: MBE-MoA1, 19; MBE-MoA10, 19; MBE-MoM5, 18
— N —
Nalamati, S.: MBE-SuM2, 17; MBE-SuM3, 17
Nelson, S.: MBE-WeA13, 24
Nepal, N.: MBE-MoA2, **19**; MBE-MoM10, 18; MBE-MoM6, 18
Norman, J.: MBE-WeA1, **24**
— O —
Okada, H.: MBE-MoP13, 20
Oktyabrsky, S.: MBE-WeA5, 24
— P —
Palmstøm, C.: MBE-WeA4, 24
Pandey, A.: MBE-MoM11, **18**
Parakh, M.: MBE-MoP11, 20
Park, K.: MBE-WeM4, 23
Pavlenko, V.: MBE-MoA5, 19
Peiris, F.: MBE-WeM13, **23**
Pinsukanjana, P.: MBE-TuM10, 21
Piyathilaka, H.: MBE-TuM13, 21
Poitras, D.: MBE-SuM5, 17
Pokharel, R.: MBE-MoP11, 20
Poole, P.: MBE-SuM5, **17**
Poungoue Mbeunmi, A.B.: MBE-SuM10, 17; MBE-SuM12, **17**
Pustovit, V.: MBE-MoA6, 19
— R —
Rasulova, G.: MBE-MoP6, **20**
Reid, E.: MBE-MoM11, 18
Reyner, C.J.: MBE-TuM12, 21
Reynolds, C.L.: MBE-SuM2, 17
Reynolds, L.: MBE-SuM3, 17
Rice, A.: MBE-WeM4, **23**
Roberts, K.: MBE-TuM13, 21
Roy, S.: MBE-WeA4, 24
Ryu, G.H.: MBE-WeA12, 24
— S —
Sadeghi, I.: MBE-SuM11, **17**
Sadowski, J.: MBE-SuM4, **17**
Santos, M.: MBE-TuM13, **21**
Saraswat, V.: MBE-MoA9, 19
Sardashti, K.: MBE-WeM10, 23
Sautter, K.: MBE-WeA4, 24
Sawicki, M.: MBE-SuM4, 17
Schmult, S.: MBE-MoM9, **18**
Scholl, E.: MBE-SuM5, 17
Schuck, C.: MBE-WeA4, **24**
Sekiguchi, H.: MBE-MoP13, **20**
Sellers, I.: MBE-TuM13, 21
Sfigakis, F.: MBE-TuM9, 21
Shabani, J.: MBE-WeM10, 23
Sharma, M.: **MBE-MoP11, 20; MBE-MoP4, 20; MBE-SuM2, 17; MBE-SuM3, 17**
Shervin, K.: MBE-TuA3, 22
Shi, Q.: MBE-SuM1, 17
Shi, Y.: MBE-TuM9, **21**
Shin, J.C.: MBE-TuM14, 21
Shin, W.: MBE-MoM11, 18
Shourov, E.H.: MBE-MoA3, **19; MBE-MoA9, 19**
Simmonds, P.: MBE-TuM1, **21; MBE-WeA4, 24**
Smith, D.: MBE-WeA10, 24; MBE-WeM1, 23
Snyder, D.: MBE-SuM3, 17
Solovyev, V.V.: MBE-MoM9, 18
Song, J.: MBE-MoP3, 20
Steenbergen, E.H.: MBE-TuM12, 21
Stevens, M.: MBE-SuM14, 17; MBE-TuM5, **21**
Storm, D.: MBE-MoA2, 19; MBE-MoM10, 18; MBE-MoM12, **18; MBE-MoM6, 18**
Strohbeen, P.J.: MBE-MoA3, 19; MBE-MoA9, **19**
Sugaya, T.: MBE-TuA1, **22**
Sun, Y.: MBE-TuA2, **22; MBE-WeA9, 24**
Sutara, F.: MBE-WeM2, 23; MBE-WeM5, 23
— T —
Tait, C.: MBE-TuM3, 21
Tam, M.C.: MBE-MoP5, 20; MBE-SuM11, 17
Tamargo, M.: MBE-WeM14, 23; MBE-WeM3, 23; MBE-WeM6, 23
Tamura, M.: MBE-MoP1, **20**
Thomas, C.: MBE-WeM11, 23; MBE-WeM9, **23**
Tian, A.: MBE-MoP12, 20
Tiedje, T.: MBE-SuM13, 17
Tokranov, V.: MBE-WeA5, 24
Tomasulo, S.: MBE-MoA11, 19; MBE-TuM11, **21**
Tracy, B.: MBE-WeM1, 23
Tran, H.: MBE-MoM14, 18
Tu, C.: MBE-TuA5, **22**
Twigg, M.: MBE-MoA11, 19; MBE-TuM11, 21
— U —
Urbas, A.: MBE-MoA6, 19
— V —
Vadiee, E.: MBE-MoM13, 18; MBE-MoM4, 18
Vallejo, K.: MBE-WeA4, 24
Vandervelde, T.: MBE-SuM14, 17; MBE-TuM5, 21
Vijayaragunathan, S.: MBE-TuM13, 21
Vurgaftman, I.: MBE-TuM11, 21
— W —
Wakahara, A.: MBE-MoP13, 20
Walters, R.: MBE-TuM11, 21
Wang, B.: MBE-TuM13, 21
Wang, T.: MBE-WeM11, 23; MBE-WeM9, 23
Wang, W.: MBE-TuA3, 22
Wasilewski, Z.R.: MBE-MoP5, 20; MBE-SuM11, 17; MBE-SuM9, 17; MBE-TuM9, 21; MBE-WeA12, 24
Webster, P.T.: MBE-TuM12, **21**
Weiss, E.: MBE-MoA12, 19
Wheeler, V.: MBE-MoA2, 19
Whiteside, V.: MBE-TuM13, 21
Wickramasinghe, K.: MBE-WeM10, **23**
Williams, R.: MBE-SuM5, 17
Wirth, S.: MBE-MoM9, 18
Wu, P.: MBE-SuM13, **17**
Wu, X.: MBE-SuM5, 17; MBE-TuM6, 21
— Y —
Yakes, M.: MBE-MoA11, **19; MBE-TuM11, 21**
Yakimov, M.: MBE-WeA5, **24**
Yamane, K.: MBE-MoP13, 20
Yang, R.Q.: MBE-TuM6, 21
Yang, S.: MBE-MoP12, 20
Yang, T.: MBE-MoP10, **20; MBE-MoP8, 20**
Yaron, N.: MBE-MoA12, 19
Yaung, K.N.: MBE-WeA9, 24
Yoo, B.: MBE-MoP3, 20
Yuan, J.: MBE-WeM10, 23
— Z —
Zang, Y.: MBE-MoP12, **20**
Zeng, J.: MBE-WeA13, 24
Zeuner, K.: MBE-SuM5, 17
Zhang, C.: MBE-WeA10, 24; MBE-WeA11, 24
Zhang, W.: MBE-MoM12, 18
Zhang, Y.: MBE-MoP8, 20
Zhang, Y.-H.: MBE-WeM1, 23
Zhang, Z.: MBE-MoP10, 20
Zugger, M.: MBE-SuM3, 17
Zwiller, V.: MBE-SuM5, 17